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October 2016

# FOD410, FOD4108, FOD4116, FOD4118 6-Pin DIP High dv/dt Zero-Cross Triac Drivers

### **Features**

- · 300 mA On-State Current
- · Zero-Voltage Crossing
- · High Blocking Voltage
  - 600 V (FOD410, FOD4116)
  - 800 V (FOD4108, FOD4118)
- · High Trigger Sensitivity
  - 1.3 mA (FOD4116, FOD4118)
  - 2 mA (FOD410, FOD4108)
- High Static dv/dt (10,000 V/µs)
- Safety and Regulatory Approvals:
  - UL1577, 5,000 VAC<sub>RMS</sub> for 1 Minute
  - DIN-EN/IEC60747-5-5

# **Applications**

- Solid-State Relays
- · Industrial Controls
- · Lighting Controls
- · Static Power Switches
- · AC Motor Starters

# **Description**

The FOD410, FOD4108, FOD4116 and FOD4118 devices consist of an infrared emitting diode coupled to a hybrid triac formed with two inverse parallel SCRs which form the triac function capable of driving discrete triacs. The FOD4116 and FOD4118 utilize a high efficiency infrared emitting diode which offers an improved trigger sensitivity. These devices are housed in a standard 6-pin dual in-line (DIP) package.

### **Functional Schematic**

# ANODE 1 CATHODE 2 \*DO NOT CONNECT (TRIAC SUBSTRATE)

# Package Outlines

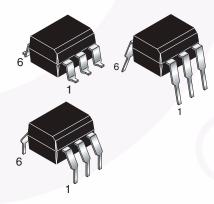


Figure 2. Package Outlines

Figure 1. Schematic

# **Safety and Insulation Ratings**

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE	< 150 V <sub>RMS</sub>	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–IV
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	V <sub>peak</sub>
V <sub>PR</sub>	Input-to-Output Test Voltage, Method B, $V_{IORM}$ x 1.875 = $V_{PR}$ , 100% Production Test with $t_m$ = 1 s, Partial Discharge < 5 pC	1594	V <sub>peak</sub>
V <sub>IORM</sub>	Maximum Working Insulation Voltage	850	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	6000	V <sub>peak</sub>
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.4	mm
T <sub>S</sub>	Case Temperature <sup>(1)</sup>	175	°C
I <sub>S,INPUT</sub>	Input Current <sup>(1)</sup>	400	mA
P <sub>S,OUTPUT</sub>	Output Power <sup>(1)</sup>	700	mW
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V <sup>(1)</sup>	> 10 <sup>9</sup>	Ω

### Note:

1. Safety limit values – maximum values allowed in the event of a failure.

# **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A = 25^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Device	Value	Unit
T <sub>STG</sub>	Storage Temperature	All	-55 to +150	°C
T <sub>OPR</sub>	Operating Temperature	All	-55 to +100	°C
T <sub>J</sub>	Junction Temperature	All	-55 to +125	°C
T <sub>SOL</sub>	Lead Solder Temperature	All	260 for 10 sec	°C
В	Total Device Power Dissipation @ 25°C	All	500	mW
P <sub>D(TOTAL)</sub>	Derate Above 25°C	All	6.6	mW/°C
EMITTER				
I <sub>F</sub>	Continuous Forward Current	All	30	mA
V <sub>R</sub>	Reverse Voltage	All	6	V
Б	Total Power Dissipation 25°C Ambient	All	50	mW
P <sub>D(EMITTER)</sub>	Derate Above 25°C	All	0.71	mW/°C
DETECTOR			<u> </u>	
M	Off State Output Terminal Voltage	FOD410, FOD4116	600	V
$V_{DRM}$	Off-State Output Terminal Voltage	FOD4108, FOD4118	800	V
I <sub>TSM</sub>	Peak Non-Repetitive Surge Current (single cycle 60 Hz sine wave)	All	3	Α
I <sub>TM</sub>	Peak On-State Current	All	300	mA
В	Total Power Dissipation @ 25°C Ambient	All	450	mW
P <sub>D(DETECTOR)</sub>	Derate Above 25°C	All	5.9	mW/°C

# **Electrical Characteristics**

 $T_A = 25$ °C unless otherwise specified.

# **Individual Component Characteristics**

Symbol	Parameter	Test Cor	nditions	Device	Min.	Тур.	Max.	Unit
EMITTER				•	•			
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 20 mA		All		1.25	1.50	V
I <sub>R</sub>	Reverse Leakage Current	V <sub>R</sub> = 6 V		All		0.0001	10	μΑ
DETECTO	OR							
Peak Blocking Currer Direction	Peak Blocking Current Either	I <sub>F</sub> = 0,	V <sub>D</sub> = 600 V	FOD410, FOD4116		3	100	
	Direction	$T_A = 100^{\circ}C^{(2)}$	V <sub>D</sub> = 800 V	FOD4108, FOD4118		3		μA
	Reverse Current T <sub>A</sub> = 100°C	T = 100°C	V <sub>D</sub> = 600 V	FOD410, FOD4116		3	100	μA
I <sub>R(RMS)</sub>		I <sub>A</sub> = 100°C	V <sub>D</sub> = 800 V	FOD4108, FOD4118				
dv/dt	Critical Rate of Rise of Off-State Voltage	I <sub>F</sub> = 0 A <sup>(3)</sup> (Figure 16)	$V_D = V_{DRM}$	All	10,000			V/µs

### Notes:

- 2. Test voltage must be applied within dv/dt rating.
- 3. This is static dv/dt. See Figure 16 for test circuit. Commutating dv/dt is a function of the load-driving thyristor(s) only.

### **Electrical Characteristics** (Continued)

 $T_A = 25$ °C unless otherwise specified.

### **Transfer Characteristics**

Symbol	Parameter	Te	st Conditions	Device	Min.	Тур.	Max.	Unit
l	LED Trigger Current	Main Terminal V	Terminal Voltage = 5 V <sup>(4)</sup>			0.65	2.0	mA
I <sub>FT</sub> LED Trigger Current		Main Terminal Voltage – 5 V		FOD4116, FOD4118		0.65	0.65 1.3	
$V_{TM}$	Peak On-State Voltage, Either Direction	I <sub>TM</sub> = 300 mA po	eak, I <sub>F</sub> = Rated I <sub>FT</sub>	All		2.2	3	V
I <sub>H</sub>	Holding Current, Either Direction	V <sub>T</sub> = 3 V		All		200	500	μΑ
ΙL	Latching Current	V <sub>T</sub> = 2.2 V		All		5		mA
t <sub>ON</sub>	Turn-On Time		V <sub>RM</sub> = V <sub>DM</sub> = 424 VAC	FOD410, FOD4116, FOD4118		60		μs
		PF = 1.0,	$V_{RM} = V_{DM} = 565 \text{ VAC}$	FOD4108				
t <sub>OFF</sub>	Turn-Off Time	I <sub>T</sub> = 300 mA	V <sub>RM</sub> = V <sub>DM</sub> = 424 VAC	FOD410, FOD4116, FOD4118		52		μs
			$V_{RM} = V_{DM} = 565 \text{ VAC}$	FOD4108				
dv/dt <sub>C</sub>	Critical Rate of Rise of Voltage at Current Com- mutation	V <sub>D</sub> = 230 V <sub>RMS</sub> , I <sub>D</sub> = 300 mA <sub>PK</sub>	$V_{\rm D}$ = 230 $V_{\rm RMS}$ , $I_{\rm D}$ = 300 mA <sub>PK</sub>			10		V/µs
di/dt <sub>C</sub>	Critical Rate of Rise of On-State Current Com- mutation	$V_D = 230 V_{RMS},$ $I_D = 300 \text{ mA}_{PK}$		All		9		A/ms
dv( <sub>IO</sub> )/dt	Critical Rate of Rise of Coupled Input/Output Voltage	I <sub>T</sub> = 0 A, V <sub>RM =</sub> V <sub>DM</sub> = 424 VAC		All	10,000			V/µs

### Note:

4. All devices are guaranteed to trigger at an I<sub>F</sub> value less than or equal to max I<sub>FT</sub>. Therefore, recommended operating I<sub>F</sub> lies between max I<sub>FT</sub> (2 mA for FOD410 and FOD4108 and 1.3 mA for FOD4116 and FOD4118) and the absolute max I<sub>F</sub> (30 mA).

# **Zero Crossing Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Тур.	Max.	Unit
V <sub>INH</sub>	Inhibit Voltage (MT1-MT2 Voltage above which device will not trigger)	I <sub>F</sub> = Rated I <sub>FT</sub>	All		8	25	٧
I <sub>DRM2</sub>	Leakage in Inhibit State	$I_F$ = Rated $I_{FT}$ , Rated $V_{DRM}$ , Off-State	All		20	200	μΑ

### **Isolation Characteristics**

Symbol	Parameter	Test Conditions	Device	Min.	Тур.	Max.	Unit
V <sub>ISO</sub>	Steady State Isolation	f = 60 Hz, t = 1 Minute <sup>(5)</sup>	All	5.000			VAC <sub>RMS</sub>
	Voltage	1 - 00 112, t - 1 Williate	All	3,000			VACRMS

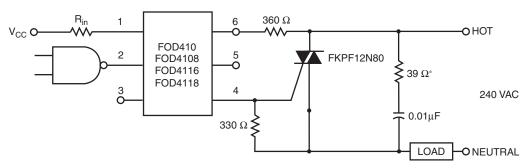
### Note:

 Isolation voltage, V<sub>ISO</sub>, is an internal device dielectric breakdown rating. For this test, pins 1, 2 and 3 are common, and pins 4, 5 and 6 are common. 5,000 VAC<sub>RMS</sub> for 1 minute duration is equivalent to 6,000 VAC<sub>RMS</sub> for 1 second duration.

# **Typical Application**

Figure 3 shows a typical circuit for when hot line switch-ing is required. In this circuit the "hot" side of the line is switched and the load connected to the cold or neutral side. The load may be connected to either the neutral or hot line.

Rin is calculated so that IF is equal to the rated IFT of the part, 2 mA for FOD410 and FOD4108, 1.3 mA for FOD4116 and FOD4118. The 39  $\Omega$  resistor and 0.01  $\mu$ F capacitor are for snubbing of the triac and may or may not be necessary depending upon the particular triac and load use.



<sup>\*</sup> For highly inductive loads (power factor < 0.5), change this value to 360 ohms.

Figure 3. Hot-Line Switching Application Circuit

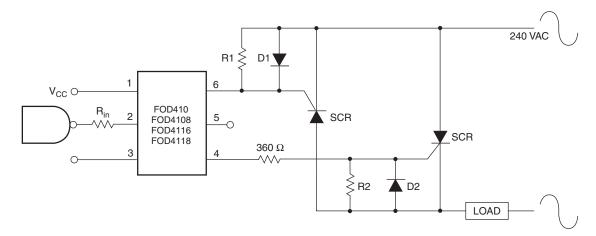


Figure 4. Inverse-Parallel SCR Driver Circuit

Suggested method of firing two, back-to-back SCR's with a Fairchild triac driver. Diodes can be 1N4001; resistors, R1 and R2, are optional 330  $\Omega$ .

Note: This optoisolator should not be used to drive a load directly. It is intended to be a discrete triac driver device only.

### **Typical Performance Characteristics** IFT - NORMALIZED LED TRIGGER CURRENT V<sub>AK</sub> = 5.0 V Normalized to T<sub>A</sub> = 25°C V<sub>F</sub> – FORWARD VOLTAGE (V) 1.4 -55°C 1.2 25°C 1.0 1.0 0.8 0.8 0.6 20 40 60 10 -60 100 IF - FORWARD CURRENT (mA) AMBIENT TEMPERATURE (°C) Figure 5. Forward Voltage Figure 6. Normalized LED Trigger Current (V<sub>F</sub>) vs. Forward Current (I<sub>F</sub>) (IFT) vs. Ambient Temperature (TA) 100 10000 $t_D = t(I_F/I_{FT\ 25^{\circ}C})$ $V_D = 400\ V_{P-P}$ $F = 60\ Hz$ If(pk) - PEAK LED CURRENT (mA) **Duty Factor** 0.005 t<sub>D</sub> – DELAY TIME (µs) 0.01 1000 0.02 10 0.2 100 10 -6 10-6 10-3 10<sup>-2</sup> 10-1 100 I<sub>FT</sub>/I<sub>F</sub> – NORMALIZED I<sub>F</sub> (mA) t - LED PULSE DURATION (s) Figure 7. Peak LED Current Figure 8. Trigger Delay Time vs. Duty Factor, Tau 1000 1.7 IFTH(PW)/IFTH(DC) - NORMALIZED IFTH V<sub>L</sub> = 250 V<sub>P-P</sub> F = 60 Hz 1.6 I<sub>TM</sub> – ON-STATE CURRENT (mA) Normalized to DC 1.5 100 1.4 1.3 T<sub>A</sub> = 100°C 1.2 T<sub>A</sub> = 25°C 10 1.1 1.0 0.9 0 200 400 600 800 1000 0 3 P<sub>W</sub> – PULSE WIDTH (µs) V<sub>TM</sub> – ON-STATE VOLTAGE (V) Figure 10. On-State Voltage Figure 9. Pulse Trigger Current (V<sub>TM</sub>) vs. On-State Current (I<sub>TM</sub>)

# **Typical Performance Characteristics** (Continued)

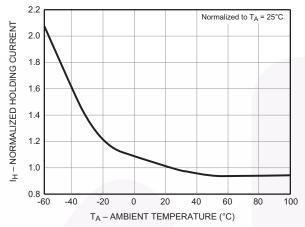


Figure 11. Normalized Holding Current (I<sub>H</sub>) vs. Ambient Temperature (T<sub>A</sub>)

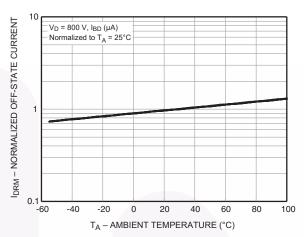


Figure 12. Normalized Off-State Current (IDRM) vs. Ambient Temperature (T<sub>A</sub>)

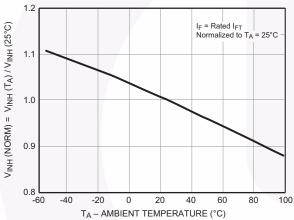


Figure 13. Normalized Inhibit Voltage (V<sub>INH</sub>) vs. Ambient Temperature (T<sub>A</sub>)

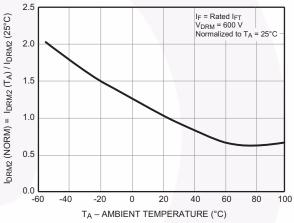


Figure 14. Normalized Leakage in Inhibit State (I<sub>DRM2</sub>) vs. Ambient Temperature (T<sub>A</sub>)

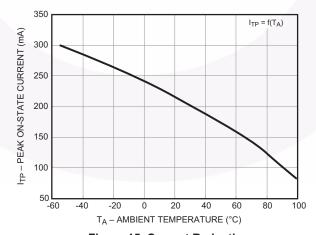


Figure 15. Current Reduction

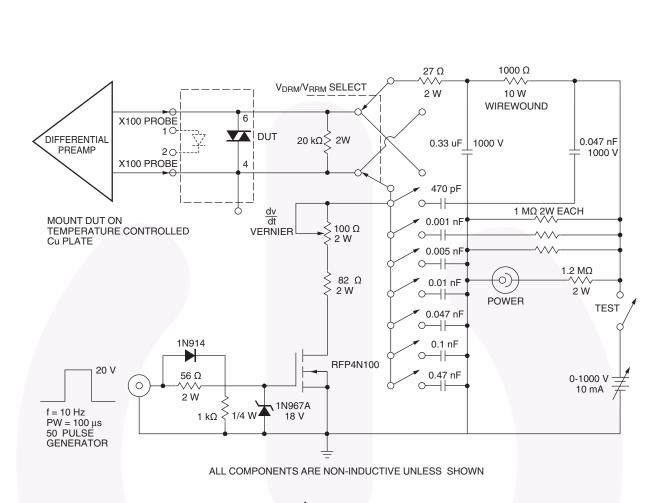
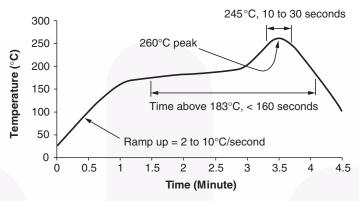


Figure 16. Circuit for Static  $\frac{dv}{dt}$  Measurement of Power Thyristors

# **Reflow Profile**



- Peak reflow temperature: 260°C (package surface temperature)
- Time of temperature higher than 183°C for 160 seconds or less
- One time soldering reflow is recommended

Figure 17. Reflow Profile

# **Ordering Information**

Part Number	Package	Packing Method
FOD410	DIP 6-Pin	Tube (50 Units)
FOD410S	SMT 6-Pin (Lead Bend)	Tube (50 Units)
FOD410SD	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
FOD410V	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
FOD410SV	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
FOD410SDV	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
FOD410TV	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

### Note:

6. The product orderable part number system listed in this table also applies to the FOD4108, FOD4116, and FOD4118 product families.

# **Marking Information**

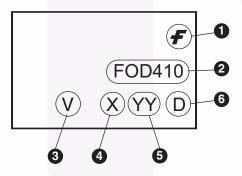
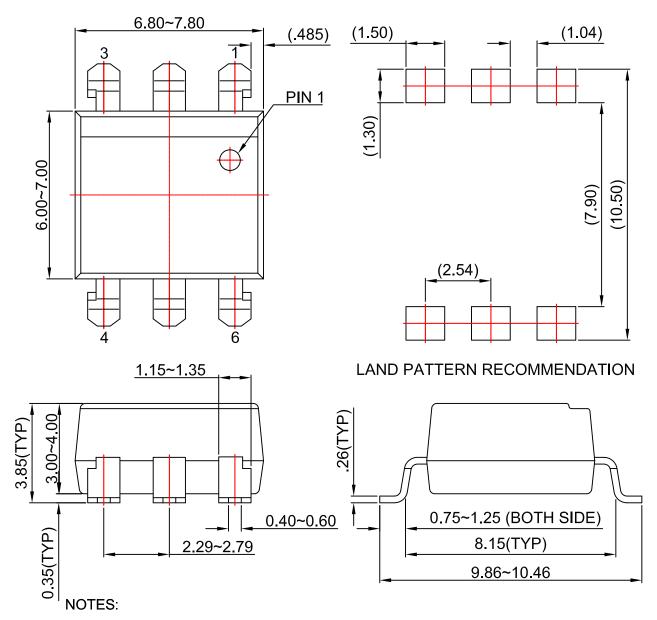


Figure 18. Top Mark

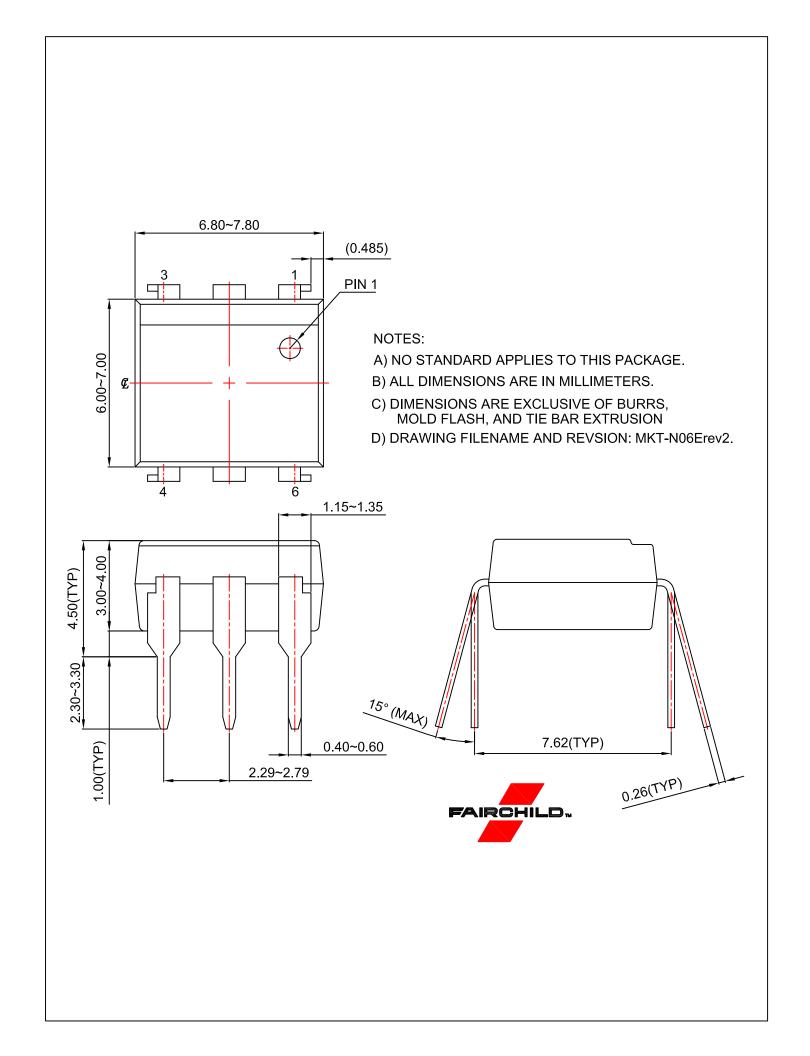
# **Table 1. Top Mark Definitions**

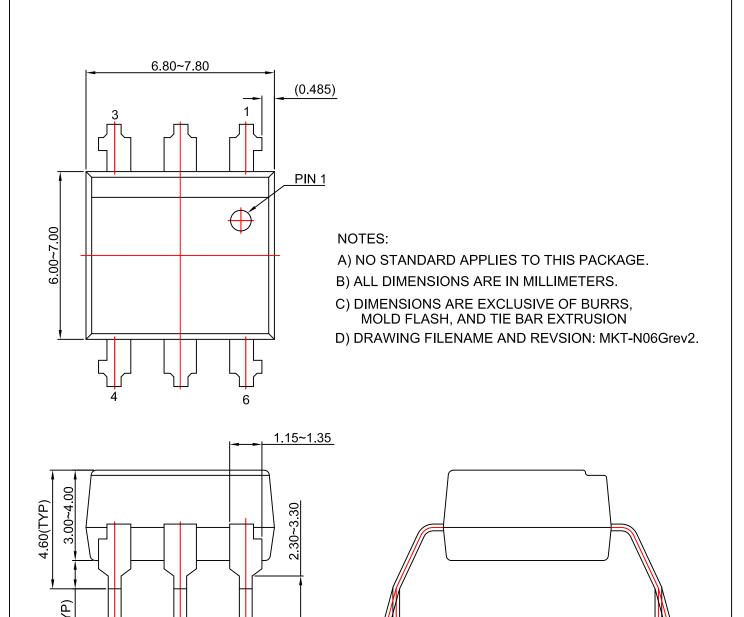
1	Fairchild Logo
2	Device Number
3	VDE mark. DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "6"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code



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